L Number	Hits	Search Text	DB	Time stamp
1	2835863	memory or storage	USPAT;	2004/06/24 15:01
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
2	140401	(memory or storage) and (nonvolatile or non-volatile or	USPAT;	2004/06/24 15:03
		floating adj gate)	US-PGPUB;	
			EPO; JPO;	
			DERWENT	
3	2068	((memory or storage) and (nonvolatile or non-volatile or	USPAT;	2004/06/24 15:03
		floating adj gate)) and capacitor and flip-flop	US-PGPUB;	
			EPO; JPO;	
4	2	(((memory or storage) and (nonvolatile or non-volatile or	DERWENT USPAT:	2004/06/24 15:05
7	2	floating adj gate)) and capacitor and flip-flop) and transistor	US-PGPUB;	2004/06/24 15:05
		with charge with capacitor with gate with boost\$5	EPO; JPO;	
		With charge with capacitor with gate with boost\$5	DERWENT	
5	4	(((memory or storage) and (nonvolatile or non-volatile or	USPAT;	2004/06/24 15:05
	'	floating adj gate)) and capacitor and flip-flop) and charge	US-PGPUB;	200 1,00,21 15.05
		with capacitor with gate with boost\$5	EPO; JPO;	
			DERWENT	